



STL140N4LLF5

N-channel 40 V, 0.00275 Ω , 32 A, PowerFLAT™ (5x6)
STripFET™ V Power MOSFET

Preliminary data

Features

Type	V _{DSS}	R _{DS(on)} max	I _D
STL140N4LLF5	40 V	0.00275 Ω	32 A ⁽¹⁾

1. The value is rated according R_{thj-pcb}.

- R_{DS(on)} * Q_g industry benchmark
- Extremely low on-resistance R_{DS(on)}
- High avalanche ruggedness
- Low gate drive power losses

Application

- Switching applications

Description

The STL140N4LLF5 is an N-channel STripFET™V Power MOSFET which has been designed to achieve very low on-state resistance providing also one of the best-in-class figure of merit (FOM).

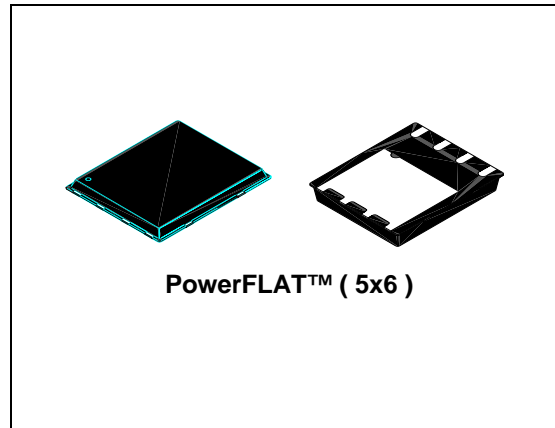


Figure 1. Internal schematic diagram

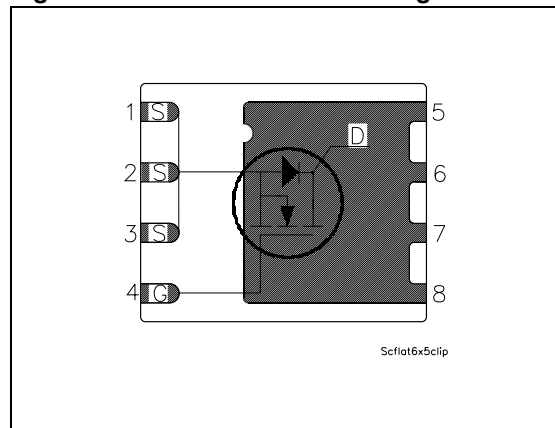


Table 1. Device summary

Order code	Marking	Package	Packaging
STL140N4LLF5	140N4LLF5	PowerFLAT™ (5x6)	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	40	V
V_{GS}	Gate-source voltage	± 22	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	140	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	88	A
$I_D^{(2)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	32	A
$I_D^{(3)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	20	A
$I_{DM}^{(3)}$	Drain current (pulsed)	128	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	80	W
$P_{TOT}^{(2)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	4	W
	Derating factor	0.03	W/ $^\circ\text{C}$
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150	$^\circ\text{C}$

1. The value is rated according R_{thj-c}
2. The value is rated according $R_{thj-pcb}$
3. Pulse width limited by safe operating area

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case (drain) (steady state)	1.56	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-ambient	31.3	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu, $t < 10$ sec

Table 4. Avalanche data

Symbol	Parameter	Value	Unit
I_{AV}	Not-repetitive avalanche current, (pulse width limited by T_J Max)	TBD	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 24\text{ V}$)	TBD	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	40			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating @ } 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 22\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 16\text{ A}$ $V_{GS} = 4.5\text{ V}$, $I_D = 16\text{ A}$		0.0021 0.0024	0.00275 0.0031	Ω Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	5900	-	pF
C_{oss}	Output capacitance			870		pF
C_{rss}	Reverse transfer capacitance			130		pF
Q_g	Total gate charge	$V_{DD} = 15\text{ V}$, $I_D = 32\text{ A}$	-	45	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 4.5\text{ V}$		TBD		nC
Q_{gd}	Gate-drain charge	(see Figure 3)		TBD		nC
R_G	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain	-	TBD	-	Ω

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 15\text{ V}$, $I_D = 16\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 2)	-	TBD	-	ns
t_r	Rise time			TBD		ns
$t_{d(off)}$	Turn-off delay time			TBD		ns
t_f	Fall time			TBD		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current		-		18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		72	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 32 \text{ A}$, $V_{GS}=0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 32 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $V_{DD} = 25 \text{ V}$	-	TBD		ns
Q_{rr}	Reverse recovery charge			TBD		nC
I_{RRM}	Reverse recovery current			TBD		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 μ s, duty cycle 1.5%

3 Test circuits

Figure 2. Switching times test circuit for resistive load

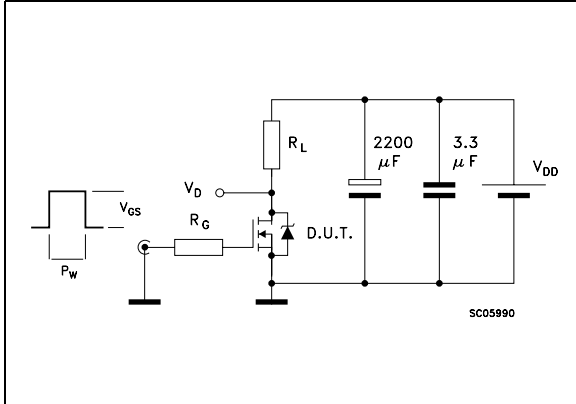


Figure 3. Gate charge test circuit

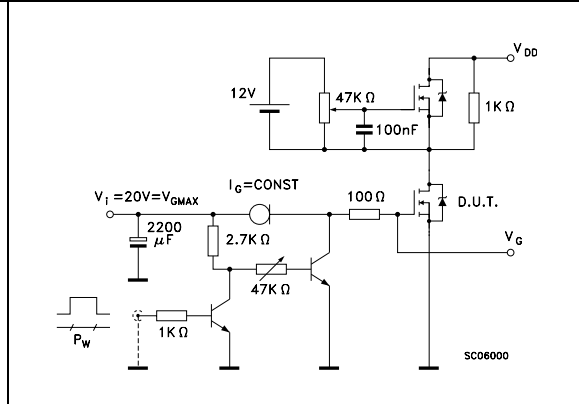


Figure 4. Test circuit for inductive load switching and diode recovery times

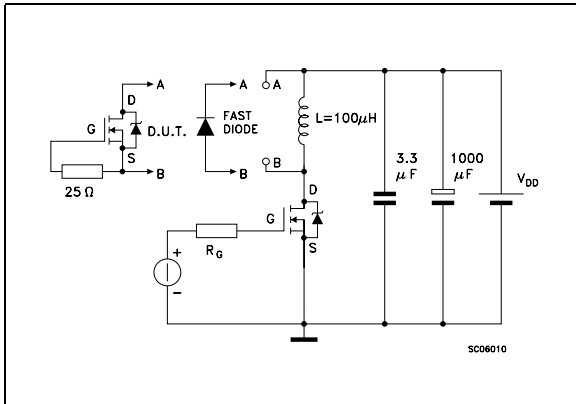


Figure 5. Unclamped inductive load test circuit

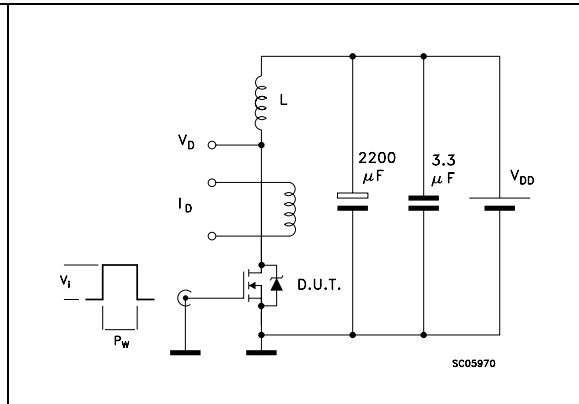


Figure 6. Unclamped inductive waveform

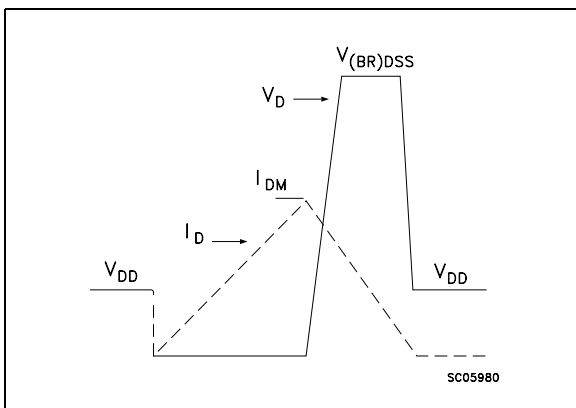
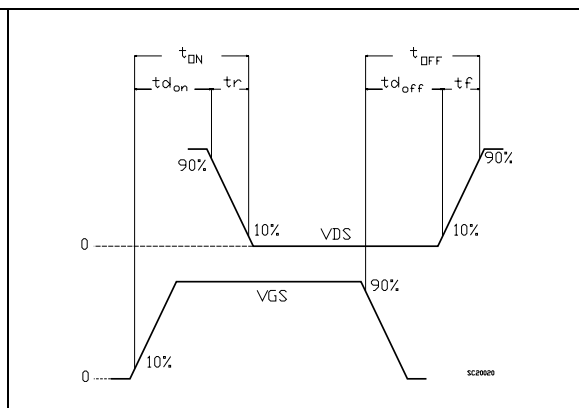


Figure 7. Switching time waveform



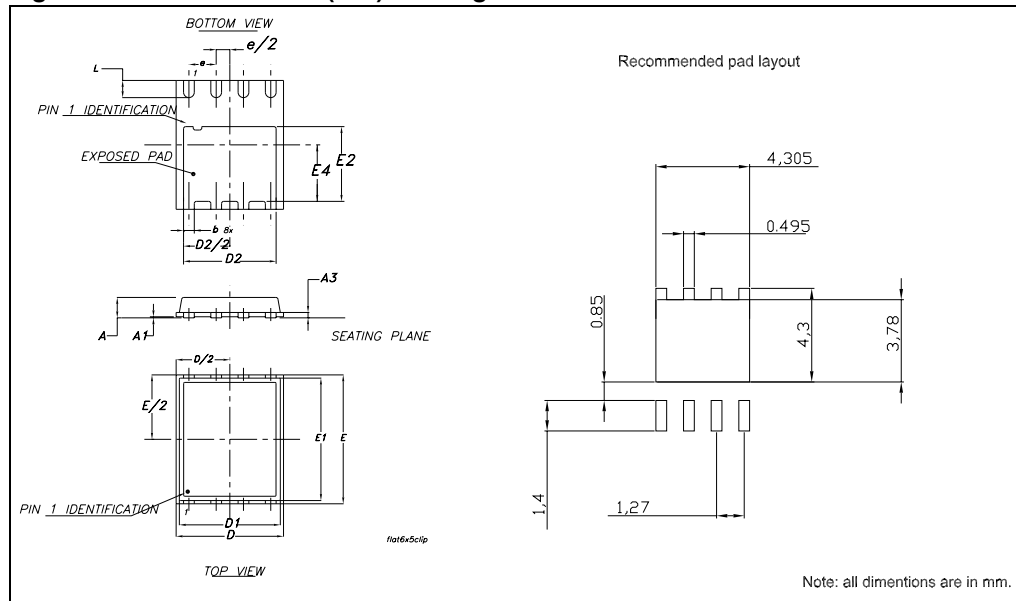
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 9. Power FLAT™ (5x6) mechanical data

Dim.	mm.			inch.		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.80	0.83	0.93	0.031	0.32	0.036
A1		0.02	0.05		0.0007	0.0019
A3		0.20			0.007	
b	0.35	0.40	0.47	0.013	0.015	0.018
D		5.00			0.196	
D1		4.75			0.187	
D2	4.15	4.20	4.25	0.163	0.165	0.167
E		6.00			0.236	
E1		5.75			0.226	
E2	3.43	3.48	3.53	0.135	0.137	0.139
E4	2.58	2.63	2.68		0.103	0.105
e		1.27			0.050	
L	0.70	0.80	0.90	0.027	0.031	0.035

Figure 8. Power FLAT™ (5x6) drawing



5 Revision history

Table 10. Document revision history

Date	Revision	Changes
03-Jun-2010	1	First release.

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